NEC

MOS FIELD EFFECT TRANSISTOR

NP55N10CLD, NP55N10DLD, NP55N10ELD

SWITCHING
N-CHANNEL POWER MOS FET
INDUSTRIAL USE

DESCRIPTION

These products are N-channel MOS Field Effect Transistor designed for high current switching applications.

ORDERING INFORMATION

PART NUMBER	PACKAGE
NP55N10CLD	TO-220AB
NP55N10DLD	TO-262
NP55N10ELD	TO-263

FEATURES

- Channel temperature 175 degree rated
- Super low on-state resistance

  $R_{DS(on)1}$ = 30 mΩ MAX. (V_{GS} = 10 V, I_D = 28 A)

★ $R_{DS(on)2}$ = 37 mΩ MAX. (V_{GS} = 5 V, I_D = 28 A)

★ • Low C_{iss} : C_{iss} = 2700 pF TYP.

- Built-in gate protection diode

ABSOLUTE MAXIMUM RATINGS (T_A = 25°C)

	Drain to Source Voltage	V_{DSS}	100	V
	Gate to Source Voltage	V_{GSS}	±20	V
	Drain Current (DC) Note1	$I_{D(DC)}$	±55	A
	Drain Current (Pulse) Note2	$I_{D(pulse)}$	±220	A
	Total Power Dissipation (T_A = 25°C)	P_T	1.8	W
	Total Power Dissipation (T_C = 25°C)	P_T	140	W
★	Single Avalanche Current Note3	I_{AS}	55 / 39 / 7	A
★	Single Avalanche Energy Note3	E_{AS}	3 / 152 / 245	mJ
	Channel Temperature	T_{ch}	175	°C
	Storage Temperature	T_{stg}	–55 to +175	°C

Notes 1. Package Limit = ± 75 A

2. PW ≤ 10 μs, Duty cycle ≤ 1 %

3. Starting T_{ch} = 25°C, R_G = 25 Ω , V_{GS} = 20 V→0 V

THERMAL RESISTANCE

Channel to Case	$R_{th(ch-C)}$	1.07	°C/W
Channel to Ambient	$R_{th(ch-A)}$	83.3	°C/W

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Not all devices/types available in every country. Please check with local NEC representative for availability and additional information.

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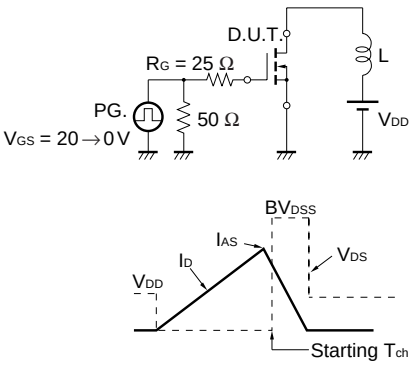
The mark ★ shows major revised points.

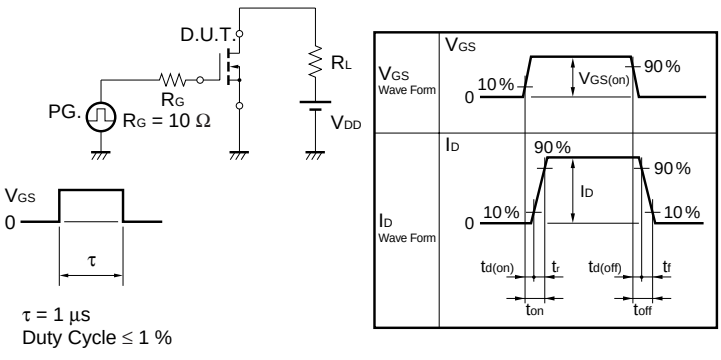
★ ELECTRICAL CHARACTERISTICS (T_A = 25 °C)

CHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Drain to Source On-state Resistance	$R_{DS(on)1}$	V_{GS} = 10 V, I_D = 28 A		21	30	mΩ
	$R_{DS(on)2}$	V_{GS} = 5 V, I_D = 28 A		27	37	mΩ
	$R_{DS(on)3}$	V_{GS} = 4.5 V, I_D = 28 A		29	40	mΩ
Gate to Source Cut-off Voltage	$V_{GS(off)}$	V_{DS} = 10 V, I_D = 250 μA	1.5	2.0	2.5	V
Forward Transfer Admittance	$\|y_{fs}\|$	V_{DS} = 10 V, I_D = 28 A	30	60		S
Drain Leakage Current	I_{DSS}	V_{DS} = 100 V, V_{GS} = 0 V			10	μA
Gate to Source Leakage Current	I_{GSS}	V_{GS} = ±20 V, V_{DS} = 0 V			±10	μA
Input Capacitance	C_{iss}	V_{DS} = 25 V, V_{GS} = 0 V, f = 1 MHz		2700	4050	pF
Output Capacitance	C_{oss}			640	960	pF
Reverse Transfer Capacitance	C_{rss}			360	540	pF
Turn-on Delay Time	$t_{d(on)}$	I_D = 28 A, $V_{GS(on)}$ = 10 V, V_{DD} = 50 V,		40	88	ns
Rise Time	t_r	R_G = 10 Ω		300	750	ns
Turn-off Delay Time	$t_{d(off)}$			220	440	ns
Fall Time	t_f			230	575	ns
Total Gate Charge	Q_{G1}	I_D = 55 A, V_{DD} = 80 V, V_{GS} = 5 V		47	71	nC
	Q_{G2}	I_D = 55 A, V_{DD} = 80 V, V_{GS} = 10 V		84	126	nC
Gate to Source Charge	Q_{GS}			11		nC
Gate to Drain Charge	Q_{GD}			31		nC
Body Diode Forward Voltage	$V_{F(S-D)}$	I_F = 55 A, V_{GS} = 0 V		1.0		V
Reverse Recovery Time	t_{rr}	I_F = 55 A, V_{GS} = 0 V, di/dt = 100 A/μs		160		ns
Reverse Recovery Charge	Q_{rr}			760		nC

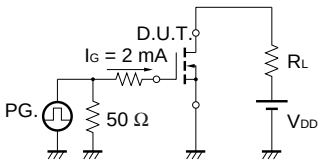
TEST CIRCUIT 1 AVALANCHE CAPABILITY



TEST CIRCUIT 2 SWITCHING TIME

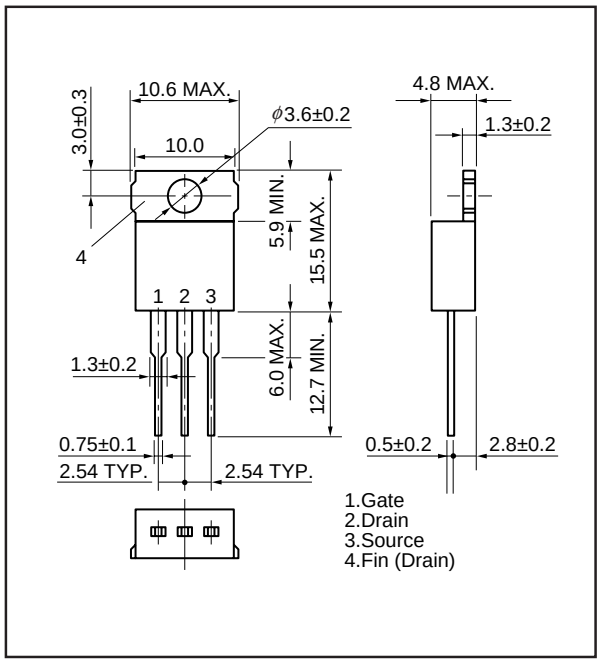


TEST CIRCUIT 3 GATE CHARGE

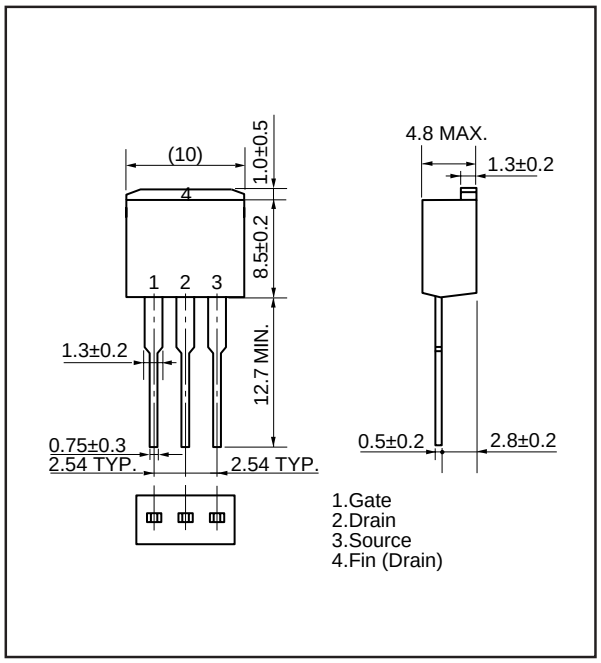


PACKAGE DRAWINGS (Unit: mm)

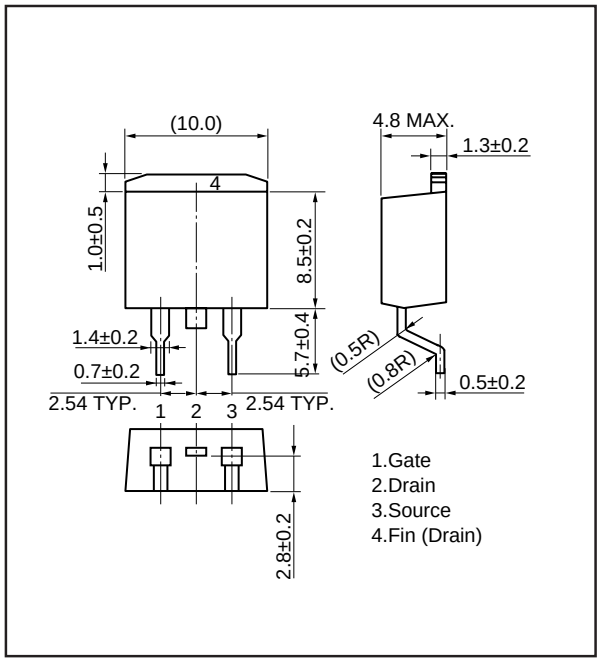
1) TO-220AB (MP-25)



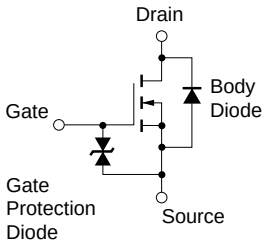
2) TO-262 (MP-25 Fin Cut)



3) TO-263 (MP-25ZJ)



EQUIVALENT CIRCUIT



Remark The diode connected between the gate and source of the transistor serves as a protector against ESD. When this device actually used, an additional protection circuit is externally required if a voltage exceeding the rated voltage may be applied to this device.

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